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Orbital selectivity and isostructural phase transitions in $AMnO_3$ – perovskites

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ABSTRACT

Oxides with perovskite structure-type containing Mn ions are well known for interesting physical phenomena, such as colossal magnetoresistance, insulator-metal transition, ferroelectricity coexisting with long range magnetic order, orbital and charge ordering, etc. DFT+DMFT methods are applied to $LaMnO_3$ and $BiMnO_3$, which are the most studied materials in the $AMnO_3$ class. Unusual electronic states with orbital selectivity are found, such as Site- and Orbital- Selective Mott state, Orbital- Selective Mott state and Mott-Band state. Some of these novel states are an alternative explanation to the previously proposed orbital disordered states, which are relevant to the phenomenology of colossal magnetoresistance phenomena. In this talk I will describe the electronic properties of these states and I will argue that these novel states are a consequence of the interplay between the orbital and electronic degrees of freedom of the manganese correlated d-electrons, the sp-electrons of the A ions and the lattice. I will show that our results are in agreement with temperature dependent resonant x-ray scattering measurements, which up to present could not be explained by other theoretical models. Using DFT+DMFT, I will propose an alternative description to the accepted Jahn-Teller phase transition mechanism in these materials. In addition, I will show that the properties of these novel orbital selective electronic states can be predicted by DFT+DMFT. This is possible due to the recent theoretical developments of forces for structural relaxations in correlated materials within the DFT+DMFT, which allows one to quantitatively study the couplings between structural and electronic degree of freedom in correlated materials.

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